

EFFECT OF PRESSURE  
ON THE PHOTOCONVERSION PARAMETERS  
OF ANISOTYPE GaSe—InSe HETEROJUNCTIONS

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S u m m a r y

Changes of the photoelectromotive force and the short-circuit current in *n*-InSe/*p*-GaSe heterojunctions stimulated by static pressure applied normally to the barrier plane have been studied. A pressure of about 35 to 40 kPa applied to optical InSe/GaSe junctions has been shown to result in almost the doubling of the open-circuit voltage and the increase of the short-circuit current by a factor not less than five. This allows us to forecast a capability to enhance the photoconversion efficiency of such heterojunctions up to 15–16%.